



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-563 Plastic-Encapsulate Transistors

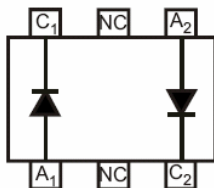
BAT54V

SCHOTTKY DIODE

FEATURES

Surface mount schottky barrier diode arrays

Marking: KAV



Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	V
Average Rectified Output Current	I _O	200	mA
Power Dissipation	P _D	150	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	833	°C/W
Storage temperature	T _{STG}	-65-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _{(BR)R}	I _R = 100μA	30		V
Reverse voltage leakage current	I _R	V _R =25V		2	uA
Forward voltage	V _F	I _F =1mA I _F =10mA I _F =30mA I _F =100mA		320 400 500 1000	mV
Total capacitance	C _T	V _R =1V,f=1MHz		10	pF
Reverse recovery time	t _{rr}	I _F =10mA, I _R =10mA~1mA R _L =100Ω		5	nS

Typical Characteristics

BAT54V

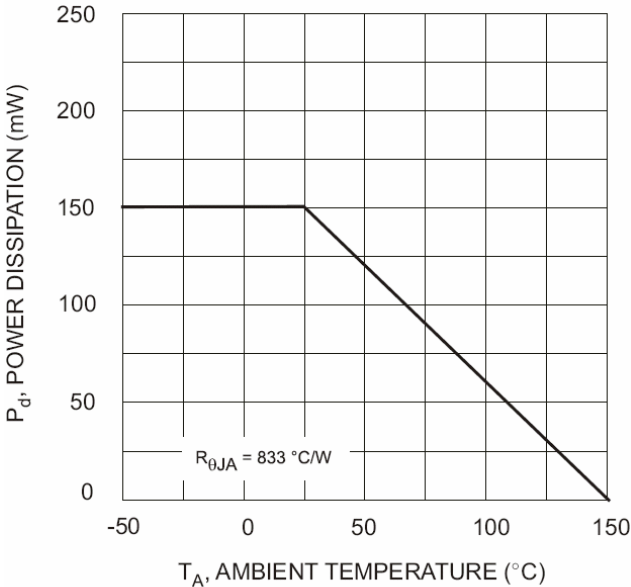


Fig. 1, Derating Curve - Total

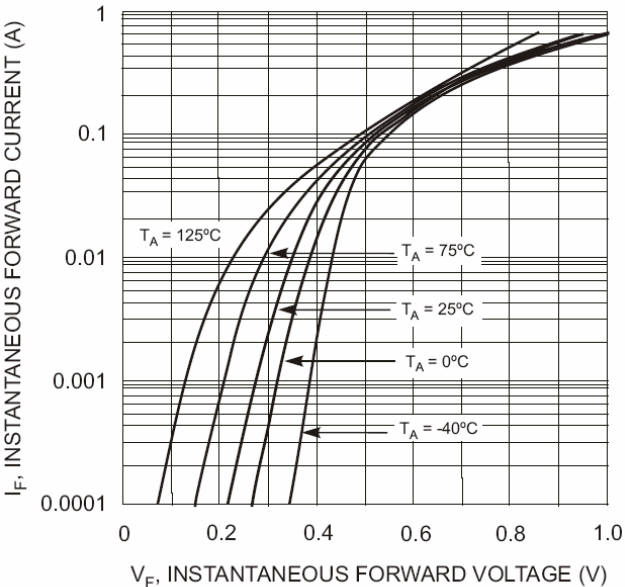


Fig. 2 Forward Characteristics

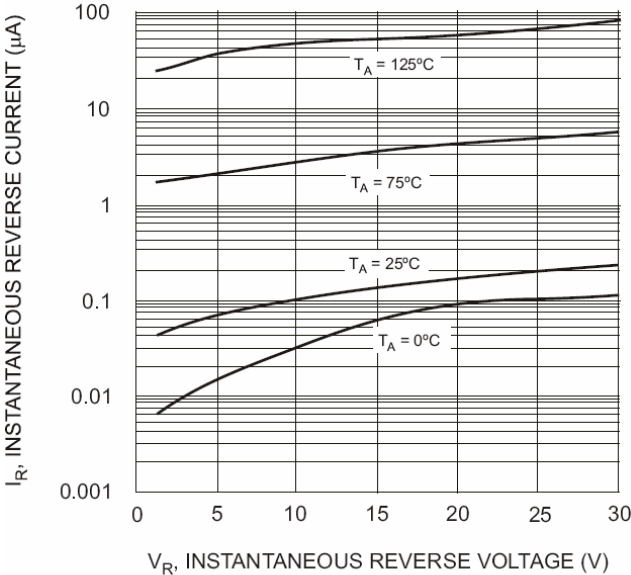


Fig. 3 Typical Reverse Characteristics

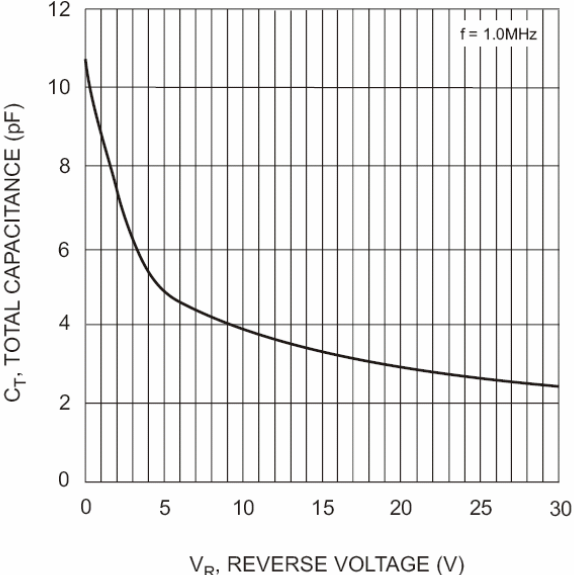


Fig. 4 Typical Capacitance vs. Reverse Voltage